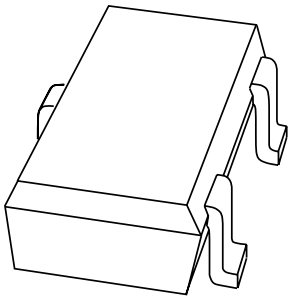
DATA SHEET



BAV199W
Low-leakage double diode

Product data sheet
Supersedes data of 1998 Jan 09

1999 May 11

Low-leakage double diode BAV199W

FEATURES

- Small plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

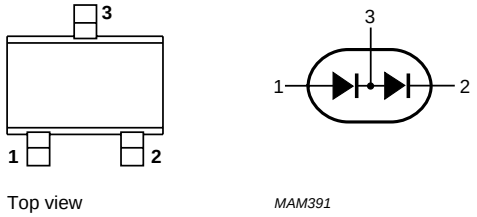
- Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small plastic SOT323 (SC-70) SMD package. The diodes are connected in series.

PINNING

PIN	DESCRIPTION
1	anode
2	cathode
3	cathode; anode



Marking code: JY- = made in Hong Kong; JYt = made in Malaysia.

Fig.1 Simplified outline (SOT323; SC-70) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode unless otherwise specified					
V_{RRM}	repetitive peak reverse voltage		–	85	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	single diode loaded; T_s = 90 °C; see Fig.2	–	135	mA
		double diode loaded; T_s = 90 °C; see Fig.2	–	110	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t_p = 1 μs	–	4	A
		t_p = 1 ms	–	1	A
		t_p = 1 s	–	0.5	A
P_{tot}	total power dissipation	single diode loaded; T_s = 90 °C	–	150	mW
		double diode loaded; T_s = 90 °C	–	240	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C

ELECTRICAL CHARACTERISTICS

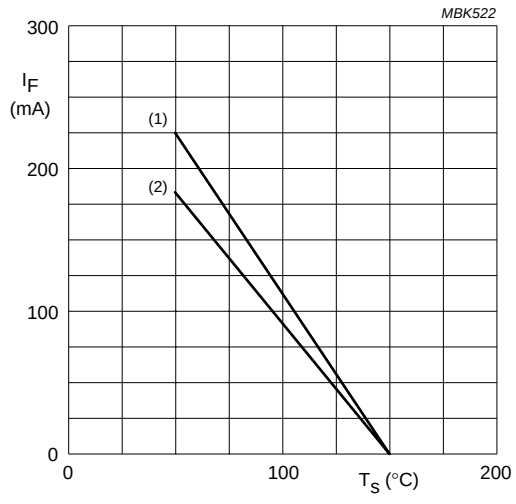
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V_F	forward voltage	see Fig.3			
		I_F = 1 mA	–	900	mV
		I_F = 10 mA	–	1000	mV
		I_F = 50 mA	–	1100	mV
		I_F = 150 mA	–	1250	mV
I_R	reverse current	see Fig.5			
		V_R = 75 V	0.003	5	nA
		V_R = 75 V; T_j = 150 °C	3	80	nA
C_d	diode capacitance	f = 1 MHz; V_R = 0; see Fig.6	2	–	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA; see Fig.7	0.8	3	μs

THERMAL CHARACTERISTICS

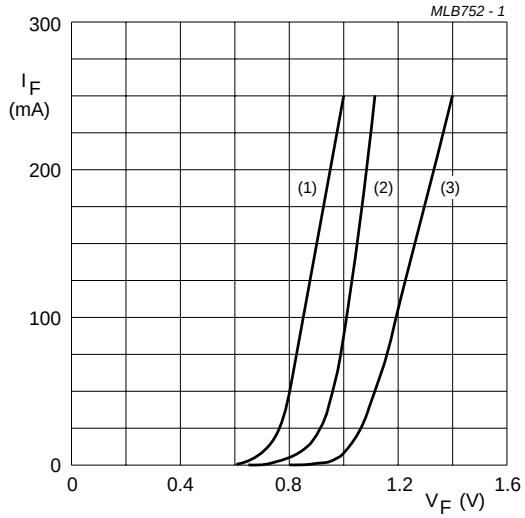
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	T_s = 90 °C	400	K/W

GRAPHICAL DATA



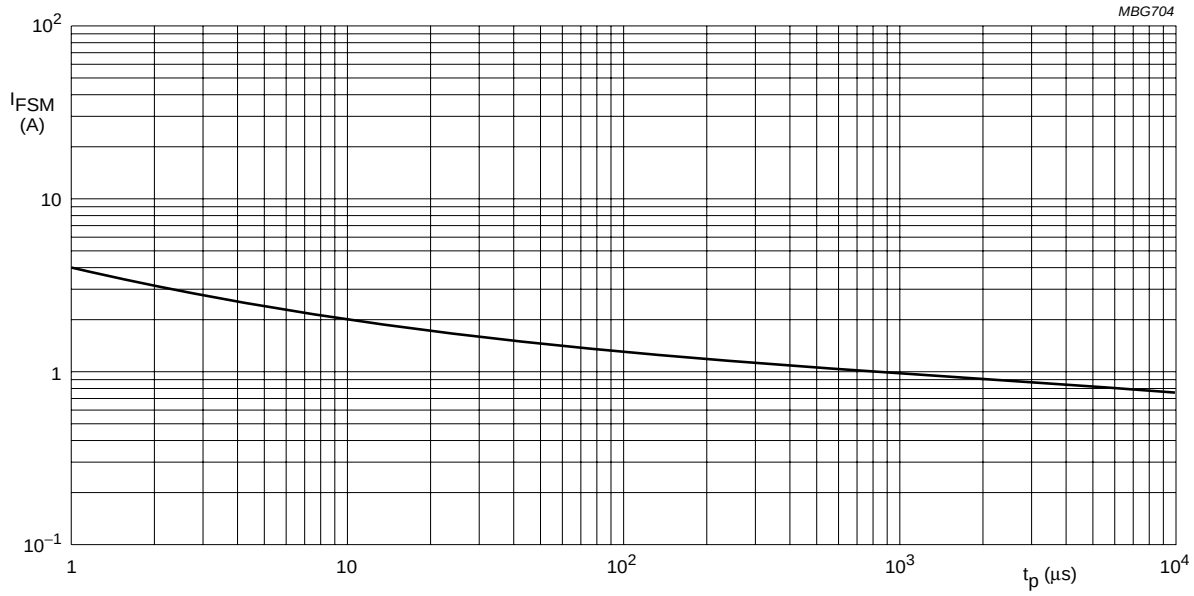
(1) Single diode loaded.
(2) Double diodes loaded.

Fig.2 Maximum permissible continuous forward current as a function of soldering point temperature; per diode.



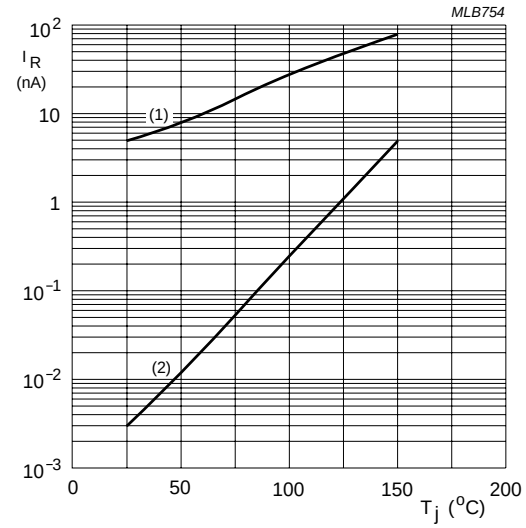
(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.



Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

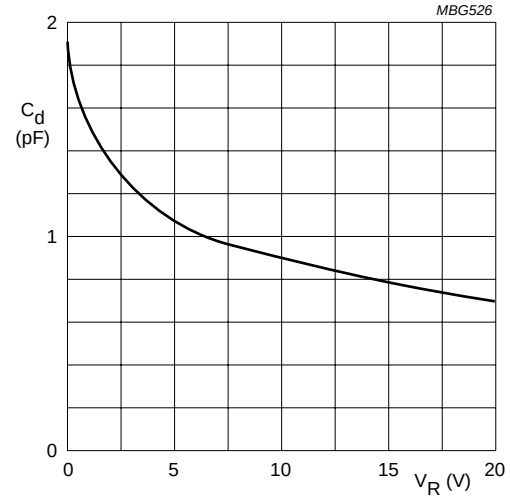


V_R = 75 V.

(1) Maximum values.

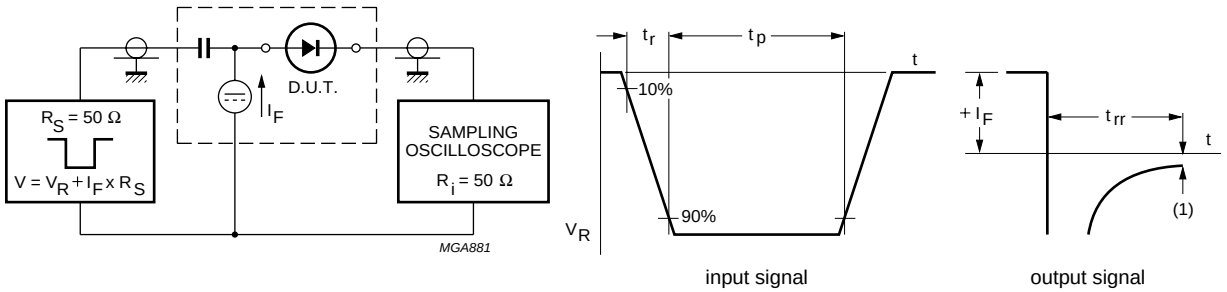
(2) Typical values.

Fig.5 Reverse current as a function of junction temperature; per diode.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; per diode; typical values.

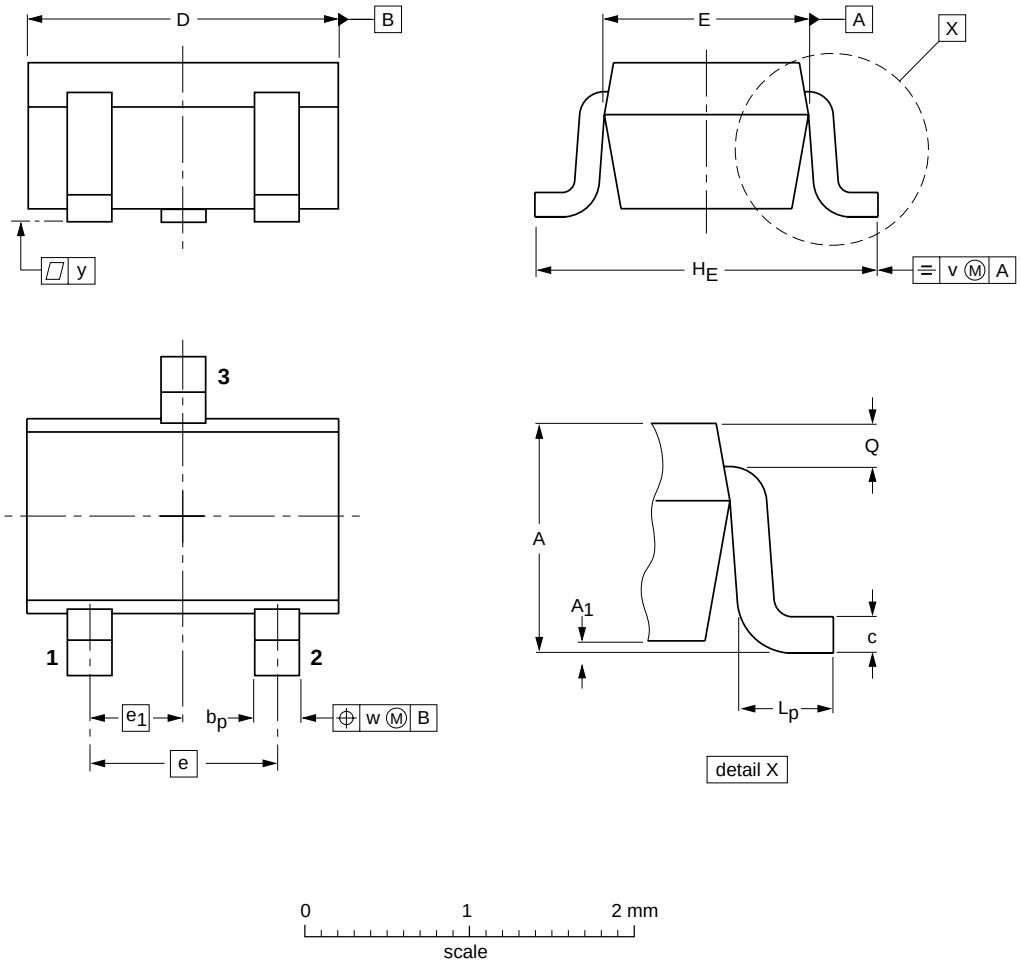


(1) I_R = 1 mA.
Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 5 μs; duty factor δ = 0.05.
Oscilloscope: rise time t_r = 0.35 ns.

Fig.7 Reverse recovery time test circuit and waveforms.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT323**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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